

Rong Zhang

List of Publications by Year in descending order

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papers

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87723

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290
all docs

290
docs citations

290
times ranked

6682
citing authors

#	ARTICLE	IF	CITATIONS
1	Planar carbon nanotube-graphene hybrid films for high-performance broadband photodetectors. Nature Communications, 2015, 6, 8589.	5.8	258
2	Progress on AlGaIn-based solar-blind ultraviolet photodetectors and focal plane arrays. Light: Science and Applications, 2021, 10, 94.	7.7	193
3	Room-temperature intrinsic ferromagnetism in epitaxial CrTe ₂ ultrathin films. Nature Communications, 2021, 12, 2492.	5.8	179
4	A robust and tuneable mid-infrared optical switch enabled by bulk Dirac fermions. Nature Communications, 2017, 8, 14111.	5.8	174
5	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase InGa ₂ O ₃ /ZnO Isotype Heterostructures. ACS Applied Materials & Interfaces, 2017, 9, 36997-37005.	4.0	158
6	Extended vapor-liquid-solid growth and field emission properties of aluminium nitride nanowires. Journal of Materials Chemistry, 2003, 13, 2024-2027.	6.7	122
7	Three-dimensional monolithic micro-LED display driven by atomically thin transistor matrix. Nature Nanotechnology, 2021, 16, 1231-1236.	15.6	120
8	On the reverse gate leakage current of AlGaIn/GaN high electron mobility transistors. Applied Physics Letters, 2010, 97, .	1.5	115
9	Evidence of Both Surface and Bulk Dirac Bands and Anisotropic Nonsaturating Magnetoresistance in ZrSiS. Advanced Electronic Materials, 2016, 2, 1600228.	2.6	115
10	Carbonized Bamboos as Excellent 3D Solar Vapor-Generation Devices. Advanced Materials Technologies, 2019, 4, 1800593.	3.0	107
11	Sensitive and Ultrabroadband Phototransistor Based on Two-Dimensional Bi ₂ O ₂ Se Nanosheets. Advanced Functional Materials, 2019, 29, 1905806.	7.8	106
12	High-Gain AlGaIn Solar-Blind Avalanche Photodiodes. IEEE Electron Device Letters, 2014, 35, 372-374.	2.2	97
13	Demonstration of the p-NiO _x /n-Ga ₂ O ₃ Heterojunction Gate FETs and Diodes With BV ² /R _{on} ,sp Figures of Merit of 0.39 GW/cm ² and 1.38 GW/cm ² . IEEE Electron Device Letters, 2021, 42, 485-488.	2.2	86
14	Electrical instability of amorphous indium-gallium-zinc oxide thin film transistors under monochromatic light illumination. Applied Physics Letters, 2012, 100, 243505.	1.5	82
15	Enhancing Magnetic Ordering in Cr-Doped Bi ₂ Se ₃ Using High-T _C Ferrimagnetic Insulator. Nano Letters, 2015, 15, 764-769.	4.5	80
16	Forward tunneling current in GaN-based blue light-emitting diodes. Applied Physics Letters, 2010, 96, .	1.5	77
17	1.37 kV/12 A NiO ^{1/2} -Ga ₂ O ₃ Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. IEEE Transactions on Power Electronics, 2021, 36, 12213-12217.	5.4	77
18	Ultra-Low Dark Current AlGaIn-Based Solar-Blind Metal-Semiconductor-Metal Photodetectors for High-Temperature Applications. IEEE Sensors Journal, 2012, 12, 2086-2090.	2.4	75

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37	Broadband hot-carrier dynamics in three-dimensional Dirac semimetal Cd ₃ As ₂ . Applied Physics Letters, 2017, 111, 091101.	1.5	42
38	Field-dependent carrier trapping induced kink effect in AlGa _N /Ga _N high electron mobility transistors. Applied Physics Letters, 2011, 98, .	1.5	40
39	Ultrafast nonlinear photoresponse of single-wall carbon nanotubes: a broadband degenerate investigation. Nanoscale, 2016, 8, 9304-9309.	2.8	39
40	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. ACS Applied Materials & Interfaces, 2019, 11, 20956-20964.	4.0	39
41	Do all screw dislocations cause leakage in Ga _N -based devices?. Applied Physics Letters, 2020, 116, .	1.5	38
42	Tellurium assisted realization of p-type N-doped ZnO. Applied Physics Letters, 2010, 96, .	1.5	36
43	Ultrafast free carrier dynamics in black phosphorus/molybdenum disulfide (BP/MoS ₂) heterostructures. Nanoscale Horizons, 2019, 4, 1099-1105.	4.1	36
44	Solar-blind ultraviolet photodetector based on vertically aligned single-crystalline In ₂ Ga ₂ O ₃ nanowire arrays. Nanophotonics, 2020, 9, 4497-4503.	2.9	35
45	Tuning the transport behavior of centimeter-scale WTe ₂ ultrathin films fabricated by pulsed laser deposition. Applied Physics Letters, 2017, 111, .	1.5	34
46	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. Advanced Materials, 2020, 32, e1904354.	11.1	34
47	Giant Topological Hall Effect in van der Waals Heterostructures of CrTe ₂ /Bi ₂ Te ₃ . ACS Nano, 2021, 15, 15710-15719.	7.3	34
48	Suppression of compensation from nitrogen and carbon related defects for p-type N-doped ZnO. Applied Physics Letters, 2009, 95, .	1.5	33
49	Vertically Emitting Indium Phosphide Nanowire Lasers. Nano Letters, 2018, 18, 3414-3420.	4.5	33
50	Carbon clusters in N-doped ZnO by metal-organic chemical vapor deposition. Applied Physics Letters, 2008, 93, 132107.	1.5	32
51	Great enhancement in the excitonic recombination and light extraction of highly ordered InGa _N /Ga _N elliptic nanorod arrays on a wafer scale. Nanotechnology, 2016, 27, 015301.	1.3	31
52	Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. IEEE Electron Device Letters, 2014, 35, 1034-1036.	2.2	30
53	Significant Performance Improvement in AlGa _N Solar-Blind Avalanche Photodiodes by Exploiting the Built-In Polarization Electric Field. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 187-192.	1.9	30
54	Transport evidence of 3D topological nodal-line semimetal phase in ZrSiS. Frontiers of Physics, 2018, 13, 1.	2.4	30

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55	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. IEEE Electron Device Letters, 2021, 42, 974-977.	2.2	29
56	Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO ₃ Epitaxial Thin Film System. Advanced Electronic Materials, 2018, 4, 1800055.	2.6	27
57	Ultrahigh Hall mobility and suppressed backward scattering in layered semiconductor Bi2O2Se. Applied Physics Letters, 2018, 113, .	1.5	27
58	Tailoring exciton dynamics of monolayer transition metal dichalcogenides by interfacial electron-phonon coupling. Communications Physics, 2019, 2, .	2.0	27
59	Significant improvements in InGaN/GaN nano-photoelectrodes for hydrogen generation by structure and polarization optimization. Scientific Reports, 2016, 6, 20218.	1.6	27
60	Highly responsive and selective ppb-level NO ₂ gas sensor based on porous Pd-functionalized CuO/rGO at room temperature. Journal of Materials Chemistry C, 2022, 10, 3756-3769.	2.7	27
61	Exploitation of Polarization in Back-Illuminated AlGaN Avalanche Photodiodes. IEEE Photonics Technology Letters, 2013, 25, 1510-1513.	1.3	25
62	Influence of thermally diffused aluminum atoms from sapphire substrate on the properties of ZnO epilayers grown by metal-organic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	0.9	24
63	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. Scientific Reports, 2019, 9, 8796.	1.6	24
64	Synthesis of Zinc Aluminate Spinel Film through the Solid-Phase Reaction between Zinc Oxide Film and Alumina Substrate. Journal of the American Ceramic Society, 2003, 86, 2059-2062.	1.9	23
65	Efficiency droop behavior of direct current aged GaN-based blue light-emitting diodes. Applied Physics Letters, 2009, 95, .	1.5	23
66	Modification of the valence band structures of polar and nonpolar plane wurtzite-GaN by anisotropic strain. Journal of Applied Physics, 2009, 106, 023714.	1.1	23
67	Manipulable and Hybridized, Ultralow-Threshold Lasing in a Plasmonic Laser Using Elliptical InGaN/GaN Nanorods. Advanced Functional Materials, 2017, 27, 1703198.	7.8	23
68	Majority and Minority Carrier Traps in NiO ₂ -Ga ₂ O ₃ p ⁺ -n Heterojunction Diode. IEEE Transactions on Electron Devices, 2022, 69, 981-987.	1.6	23
69	Achieving Record High External Quantum Efficiency >86.7% in Solar-Blind Photoelectrochemical Photodetection. Advanced Functional Materials, 2022, 32, .	7.8	23
70	C-Plane Blue Micro-LED With 1.53 GHz Bandwidth for High-Speed Visible Light Communication. IEEE Electron Device Letters, 2022, 43, 910-913.	2.2	23
71	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. Scientific Reports, 2016, 6, 23486.	1.6	21
72	Controllable synthesis and magnetotransport properties of Cd ₃ As ₂ Dirac semimetal nanostructures. RSC Advances, 2017, 7, 17689-17696.	1.7	21

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73	Gate Reliability of p-GaN Gate AlGaIn/GaN High Electron Mobility Transistors. IEEE Electron Device Letters, 2019, 40, 379-382.	2.2	21
74	Characteristics of polarization-doped N-face III-nitride light-emitting diodes. Applied Physics Letters, 2012, 100, 073507.	1.5	20
75	Temperature-dependent photoluminescence of ZnO films codoped with tellurium and nitrogen. Journal of Applied Physics, 2012, 112, 103534.	1.1	20
76	1.4-kV Quasi-Vertical GaN Schottky Barrier Diode With Reverse $p-n$ Junction Termination. IEEE Journal of the Electron Devices Society, 2020, 8, 316-320.	1.2	20
77	3.4-kV AlGaIn/GaN Schottky Barrier Diode on Silicon Substrate With Engineered Anode Structure. IEEE Electron Device Letters, 2021, 42, 208-211.	2.2	20
78	Highly efficient solar steam generation by hybrid plasmonic structured TiN/mesoporous anodized alumina membrane. Journal of Materials Research, 2018, 33, 3857-3869.	1.2	19
79	High- k HfO ₂ -Based AlGaIn/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. IEEE Journal of the Electron Devices Society, 2020, 8, 15-19.	1.2	19
80	High-Responsivity Graphene/4H-SiC Ultraviolet Photodetector Based on a Planar Junction Formed by the Dual Modulation of Electric and Light Fields. Advanced Optical Materials, 2020, 8, 2000559.	3.6	19
81	Investigations of Sidewall Passivation Technology on the Optical Performance for Smaller Size GaN-Based Micro-LEDs. Crystals, 2021, 11, 403.	1.0	19
82	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. IEEE Transactions on Power Electronics, 2021, 36, 12163-12167.	5.4	19
83	70- μ m-Body Ga ₂ O ₃ Schottky Barrier Diode With 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. IEEE Electron Device Letters, 2022, 43, 773-776.	2.2	19
84	Ga ₂ O ₃ /GaN Heterostructural Ultraviolet Photodetectors with Exciton-Dominated Ultranarrow Response. ACS Applied Electronic Materials, 2022, 4, 188-196.	2.0	19
85	High Quantum Efficiency Back-Illuminated AlGaIn-Based Solar-Blind Ultraviolet $p-n$ Photodetectors. Chinese Physics Letters, 2012, 29, 097302.	1.3	18
86	Intramolecular Crystal Nucleation Favored by Polymer Crystallization: Monte Carlo Simulation Evidence. Journal of Physical Chemistry B, 2016, 120, 6754-6760.	1.2	18
87	Localized Surface Plasmon-Enhanced Deep-UV Light-Emitting Diodes with Al/Al ₂ O ₃ Asymmetrical Nanoparticles. Plasmonics, 2017, 12, 843-848.	1.8	18
88	Suppressed carrier density for the patterned high mobility two-dimensional electron gas at β -Al ₂ O ₃ /SrTiO ₃ heterointerfaces. Applied Physics Letters, 2017, 111, 021602.	1.5	18
89	Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite CH ₃ NH ₃ Pb(BrxI _{1-x}) ₃ Crystals Synthesized via a Solvothermal Method. Scientific Reports, 2017, 7, 17695.	1.6	18
90	Experimental observation of dual magnetic states in topological insulators. Science Advances, 2019, 5, eaav2088.	4.7	18

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91	Anion Engineering Enhanced Response Speed and Tunable Spectral Responsivity in Gallium-Oxynitrides-Based Ultraviolet Photodetectors. ACS Applied Electronic Materials, 2020, 2, 808-816.	2.0	18
92	Investigation of the Electroluminescence Mechanism of GaN-Based Blue and Green Light-Emitting Diodes with Junction Temperature Range of 120â€“373 K. Applied Sciences (Switzerland), 2020, 10, 444.	1.3	18
93	1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. IEEE Transactions on Power Electronics, 2022, 37, 26-30.	5.4	18
94	Solar-blind ultraviolet AlInN/AlGaIn distributed Bragg reflectors. Applied Physics Letters, 2013, 102, .	1.5	17
95	Enhanced p-type conduction in AlGaIn grown by metal-source flow-rate modulation epitaxy. Applied Physics Letters, 2018, 113, .	1.5	17
96	V_T Shift and Recovery Mechanisms of p-GaN Gate HEMTs Under DC/AC Gate Stress Investigated by Fast Sweeping Characterization. IEEE Electron Device Letters, 2021, 42, 1508-1511.	2.2	17
97	Growth of In-rich and Ga-rich InGaIn alloys by MOCVD and fabrication of InGaIn-based photoelectrodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1817-1820.	0.8	16
98	High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. IEEE Photonics Technology Letters, 2016, 28, 2526-2528.	1.3	16
99	High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. IEEE Photonics Technology Letters, 2016, 28, 1189-1192.	1.3	16
100	Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. IEEE Transactions on Electron Devices, 2017, 64, 4532-4539.	1.6	16
101	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. IEEE Electron Device Letters, 2020, 41, 469-472.	2.2	16
102	Influence of vapor transport equilibration on the crystal quality and thermal-expansion coefficients of $\text{In}^3\text{-LiAlO}_2$. Journal of Applied Physics, 2005, 98, 084909.	1.1	15
103	4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. IEEE Photonics Journal, 2016, 8, 1-7.	1.0	15
104	A Terahertz Controlled NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. Advanced Optical Materials, 2017, 5, 1700108.	3.6	15
105	$\text{In}^2\text{-Ga}_2\text{O}_3$: A Promising Candidate for High-Electron-Mobility Transistors. IEEE Electron Device Letters, 2020, , 1-1.	2.2	15
106	Band Alignment and Enhanced Interfacial Conductivity Manipulated by Polarization in a Surfactant-Mediated Grown $\text{In}^2\text{-Ga}_2\text{O}_3/\text{In}^2\text{-Ga}_2\text{O}_3$ Heterostructure. ACS Applied Electronic Materials, 2021, 3, 795-803.	2.0	15
107	Demonstration of $\text{In}^2\text{-Ga}_2\text{O}_3$ Superjunction-Equivalent MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 2203-2209.	1.6	15
108	Study on strain and piezoelectric polarization of AlN thin films grown on Si. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 628-630.	0.9	14

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109	High-temperature and reliability performance of 4H-SiC Schottky-barrier photodiodes for UV detection. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, .	0.6	14
110	First-principles insights on the electronic and optical properties of ZnO@CNT core@shell nanostructure. <i>Scientific Reports</i> , 2018, 8, 15464.	1.6	14
111	Photoresponsivity of an all-semimetal heterostructure based on graphene and WTe ₂ . <i>Scientific Reports</i> , 2018, 8, 12840.	1.6	14
112	Electrolyte gate controlled metal-insulator transitions of the CaZrO ₃ /SrTiO ₃ heterointerface. <i>Applied Physics Letters</i> , 2019, 115, 061601.	1.5	14
113	High-Responsivity and Fast-Response Ultraviolet Phototransistors Based on Enhanced p-GaN/AlGaIn/GaN HEMTs. <i>ACS Photonics</i> , 2022, 9, 2040-2045.	3.2	14
114	Ge composition and temperature dependence of the deposition of SiGe layers. <i>Journal of Applied Physics</i> , 1994, 75, 5382-5384.	1.1	13
115	An Improved Design for Solar-Blind AlGaIn Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.	1.0	13
116	4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.	1.0	13
117	Topological Phase Transition-Induced Triaxial Vector Magnetoresistance in (Bi _{1-x} In _x) ₂ Se ₃ Nanodevices. <i>ACS Nano</i> , 2018, 12, 1537-1543.	7.3	13
118	High Sensitive pH Sensor Based on AlInN/GaN Heterostructure Transistor. <i>Sensors</i> , 2018, 18, 1314.	2.1	13
119	Janus Ga ₂ SeTe: A Promising Candidate for Highly Efficient Solar Cells. <i>Solar Rrl</i> , 2019, 3, 1900321.	3.1	13
120	Ultrafast Orbital-Oriented Control of Magnetization in Half-Metallic La _{0.7} Sr _{0.3} MnO ₃ Films. <i>Advanced Materials</i> , 2019, 31, e1806443.	11.1	13
121	Effect of Current on the Inhomogeneous Light Emission From AlGaInP-Based Flip-Chip Red Mini-LEDs. <i>IEEE Electron Device Letters</i> , 2022, 43, 402-405.	2.2	13
122	GaN MSM photodetectors fabricated on bulk GaN with low dark-current and high UV/visible rejection ratio. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2473-2475.	0.8	12
123	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. <i>Scientific Reports</i> , 2017, 7, 7503.	1.6	12
124	Strong interface-induced spin-charge conversion in YIG/Cr heterostructures. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	12
125	Spatially localised luminescence emission properties induced by formation of ring-shaped quasi-potential trap around V-pits in InGaIn epi-layers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 2823-2827.	0.8	11
126	Nontrivial surface state transport in Bi ₂ Se ₃ topological insulator nanoribbons. <i>Applied Physics Letters</i> , 2017, 110, 053108.	1.5	11

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127	M-Plane $\hat{\Gamma}$ -Ga _{0.5} O _{0.5} Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. IEEE Electron Device Letters, 2022, 43, 541-544.	2.2	11
128	Mutually beneficial doping of tellurium and nitrogen in ZnO films grown by metal-organic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	0.9	10
129	The temperature dependence of optical properties of InGaN alloys. Science China: Physics, Mechanics and Astronomy, 2012, 55, 396-399.	2.0	10
130	Distinct enhancement of sub-bandgap photoresponse through intermediate band in high dose implanted ZnTe:O alloys. Scientific Reports, 2017, 7, 44399.	1.6	10
131	Bandgap renormalization in single-wall carbon nanotubes. Scientific Reports, 2017, 7, 11221.	1.6	10
132	Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. IEEE Photonics Technology Letters, 2017, 29, 1603-1606.	1.3	10
133	Layered Topological Insulators and Semimetals for $\hat{\Gamma}$ Magnetoresistance Type Sensors. Advanced Quantum Technologies, 2019, 2, 1800039.	1.8	10
134	Observation of bimolecular recombination in high mobility semiconductor Bi ₂ O ₂ Se using ultrafast spectroscopy. Applied Physics Letters, 2018, 113, 061104.	1.5	10
135	Precise Extraction of Dynamic $\langle i \rangle_{\text{dson}}$ Under High Frequency and High Voltage by a Double-Diode-Isolation Method. IEEE Journal of the Electron Devices Society, 2019, 7, 690-695.	1.2	10
136	Single-crystal GaN layer converted from $\hat{\Gamma}$ ² -Ga ₂ O ₃ films and its application for free-standing GaN. CrystEngComm, 2019, 21, 1224-1230.	1.3	10
137	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. IEEE Electron Device Letters, 2019, 40, 1929-1932.	2.2	10
138	Performance Modulation for Back-Illuminated AlGa _N Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. IEEE Photonics Journal, 2019, 11, 1-7.	1.0	10
139	Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. Small, 2020, 16, 1906205.	5.2	10
140	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. IEEE Photonics Technology Letters, 2020, 32, 791-794.	1.3	10
141	Growth and nitridation of $\hat{\Gamma}$ ² -Ga ₂ O ₃ thin films by Sol-Gel spin-coating epitaxy with post-annealing process. Journal of Sol-Gel Science and Technology, 2021, 100, 183-191.	1.1	10
142	Field-Plated NiO/Ga ₂ O ₃ p-n Heterojunction Power Diodes With High-Temperature Thermal Stability and Near Unity Ideality Factors. IEEE Journal of the Electron Devices Society, 2021, 9, 1166-1171.	1.2	10
143	Self-Intercalation Tunable Interlayer Exchange Coupling in a Synthetic van der Waals Antiferromagnet. Advanced Functional Materials, 2022, 32, .	7.8	10
144	Simulation model to very low pressure chemical vapor deposition of SiGe alloy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 3256-3260.	0.9	9

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145	Epitaxial growth of ZnO films on (100) and (001) \hat{I}^3 -LiAlO ₂ substrates by pulsed laser deposition. Journal of Materials Science, 2006, 41, 5937-5940.	1.7	9
146	Self-assembly of Polyaniline: Mechanism Study. Chinese Journal of Chemical Physics, 2008, 21, 187-192.	0.6	9
147	Mn incorporation induced changes on structure and properties of N-doped ZnO. Journal of Applied Physics, 2009, 106, 113710.	1.1	9
148	Temperature-dependent exciton-related transition energies mediated by carrier concentrations in unintentionally Al-doped ZnO films. Applied Physics Letters, 2013, 102, 221905.	1.5	9
149	Demonstration of an AlGaIn-based solar-blind high-voltage photoconductive switch. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, 040601.	0.6	9
150	Intrinsic Topological Insulator Bi _{1.5} Sb _{0.5} Te _{3-x} Sex Thin Crystals. Scientific Reports, 2015, 5, 7931.	1.6	9
151	Polarized Emission From InGaIn/GaN Single Nanorod Light-Emitting Diode. IEEE Photonics Technology Letters, 2016, 28, 721-724.	1.3	9
152	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. IEEE Photonics Technology Letters, 2018, 30, 805-808.	1.3	9
153	Polarization-independent Indium Phosphide Nanowire Photodetectors. Advanced Optical Materials, 2020, 8, 2000514.	3.6	9
154	Over 1200 V Normally-OFF p-NiO Gated AlGaIn/GaN HEMTs on Si With a Small Threshold Voltage Shift. IEEE Electron Device Letters, 2022, 43, 268-271.	2.2	9
155	A modified simplified coherent potential approximation model of band gap energy of III-V ternary alloys. Science China: Physics, Mechanics and Astronomy, 2012, 55, 400-403.	2.0	8
156	Thermal pretreatment of sapphire substrates prior to ZnO buffer layer growth. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 051203.	0.6	8
157	Evidence for ferromagnetic coupling at the doped topological insulator/ferrimagnetic insulator interface. AIP Advances, 2016, 6, 055813.	0.6	8
158	High-Quality Crystal Growth and Characteristics of AlGaIn-Based Solar-Blind Distributed Bragg Reflectors with a Tri-layer Period Structure. Scientific Reports, 2016, 6, 29571.	1.6	8
159	Probing the Buried Magnetic Interfaces. ACS Applied Materials & Interfaces, 2016, 8, 5752-5757.	4.0	8
160	Fine Control of the Electric Field Distribution in the Heterostructure Multiplication Region of AlGaIn Avalanche Photodiodes. IEEE Photonics Journal, 2017, 9, 1-7.	1.0	8
161	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. IEEE Photonics Journal, 2017, 9, 1-8.	1.0	8
162	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Core-Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. ACS Nano, 2018, 12, 7327-7334.	7.3	8

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163	Charge transfer dynamics of the CdTe quantum dots fluorescence quenching induced by ferrous (II) ions. <i>Applied Physics Letters</i> , 2020, 116, 012105.	1.5	8
164	Enhancing deep-UV emission at 234 nm by introducing a truncated pyramid AlN/GaN nanostructure with fine-tuned multiple facets. <i>Nanoscale</i> , 2022, 14, 653-662.	2.8	8
165	Unlocking the Single-Domain Heteroepitaxy of Orthorhombic Ga_2O_3 via Phase Engineering. <i>ACS Applied Electronic Materials</i> , 2022, 4, 461-468.	2.0	8
166	Band alignment and polarization engineering in $\text{Ga}_2\text{O}_3/\text{GaN}$ ferroelectric heterojunction. <i>Science China: Physics, Mechanics and Astronomy</i> , 2022, 65, .	2.0	8
167	Microstructures of AlGaIn/Si (111) Grown by Metalorganic Chemical Vapor Deposition. <i>Physica Status Solidi A</i> , 2002, 191, 137-142.	1.7	7
168	Structural properties of GaN(0001) epitaxial layers revealed by high resolution X-ray diffraction. <i>Science China: Physics, Mechanics and Astronomy</i> , 2010, 53, 68-71.	2.0	7
169	The parameters in the band-anticrossing model for $\text{In}_x\text{Ga}_{1-x}\text{N}_y\text{P}_{1-y}$ before and after annealing. <i>Science China: Physics, Mechanics and Astronomy</i> , 2011, 54, 2160-2163.	2.0	7
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171	Solar-blind ultraviolet band-pass filter based on metal-dielectric multilayer structures. <i>Chinese Physics B</i> , 2014, 23, 074201.	0.7	7
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